

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-17 (Canceled).

Claim 18 (New): A semiconductor device comprising:

a semiconductor substrate;

a gate oxide film formed on an element forming region of the semiconductor substrate;

a shallow trench insulation film formed in an element isolation region of the semiconductor substrate; and

a gate electrode film formed on the gate oxide film;

wherein the shallow trench insulation film has an upper surface positioned at a height between an upper surface and lower surface of the gate electrode film and the gate oxide film is doped with boron.